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	Search Terms	Total	USPAT	USOCR	EPO
1	FULL	521273			
2	IMAGE	320873	***************************************		***************************************
3	P-SURFACE	42			***************************************
4	SURROUND	81363			***************************************
5	VISIBLE	229879			***************************************
6	WORLD	64128			***************************************
7	(P-SURFACE AND 6)	1			***************************************

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	ับ	1	Document	ID	Issue Date	Pages
1			US 5487172	A	19960123	508

	Title	Current OR	Current XRef
1	Transform processor system having reduced processing bandwith	712/32	700/8 ;

	Retrieval Classif	Inventor			С	P	2	3	4	5
1		Hyatt,	Gilbert P.	⊠						

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	U	1	D	ocument	ID	Issue Date	Pages
1	☒		US	6018171	A	20000125	12
2	⊠		US	5260639	A	19931109	
3	⊠		US	RE29845	E	19781121	
4	☒		US	RE29648	E	19780530	
5	⊠		US	4001056	Α		
6	Ø		US	3931631	A	19760106	
7	⊠		us	3873382	Α	19750 [.]	
8	☒		US	3803427	А	19740409	

	Title
Shal	low junction ferroelectric memory cell having a laterally extending
	p-n junction and method of making the same
ſeth	od for remotely powering a device such as a lunar rover
aAs	.sub.1-x P.sub.x electroluminescent device doped with isoelectronic
	impurities
Proc	ess for the preparation of electroluminescent III-V materials
	containing isoelectronic impurities
Cpit	axial deposition of III-V compounds containing isoelectronic impurities
Epit	
Gall	impurities

	Current OR	Current XRef	Retrieval Classif	. Inventor	s
1	257/295	257/256 ; 438/3 ; 438/957		Hsu, Sheng Teng , et al.	
2	322/2R	136/292 ; 244/1R ; 372/43		De Young, Russell J. , et al.	
3	257/87			Groves, Warren O., et al.	
4	438/37	117/105 ; 257/101 ; 257/102 ; 313/103R ; 438/45		Groves, Warren O. , et al.	
5	438/37	117/105 ; 117/89 ; 117/954 ; 117/955 ; 148/DIG.110 ; 148/DIG.99 ; 257/87 ; 313/498 ; 438/45		Groves, Warren O.,, et al.	
6	257/87	438/46		Groves, Warren O. , et al.	
7	438/508	117/89 ; 148/DIG.65 ; 148/DIG.72 ; 252/950 ; 252/951 ; 257/79 ; 313/499 ; 438/37 ; 438/925 ; 438/936		Öroves, Warren Olley , et al.	
8	327/119			Brodzinksy, Albert	

	Ŭ	1	Document ID	Issue Date	Pages
9			US 3725749 A	19730403	
10	⊠		US 3649890 A	19720.314	
11	☒		US 3617820 A	19711102	

 Title
GaAS P ELECTROLUMINESCENT DEVICE DOPED WITH ISOELECTRONIC IMPURITIES
HIGH BURNOUT RESISTANCE SCHOTTKY BARRIER DIODE
INJECTION-LUMINESCENT DIODES

	Current OR	Current XRef	Retrieval Classif	Inventor	s
9	257/87	148/DIG.107 ; 148/DIG.119 ; 148/DIG.135 ; 148/DIG.49 ; 148/DIG.56 ; 148/DIG.57 ; 148/DIG.65 ; 148/DIG.67 ; 148/DIG.72 ; 148/DIG.99 ; 438/37 ; 438/46 ; 438/918		Groves, Warren Olley, et al.	
10	257/484	257/428 ; 257/735 ; 257/773 ; 257/785		Howell, Charles M. , et al.	
11	257/86	148/DIG.119 ; 148/DIG.56 ; 148/DIG.65 ; 148/DIG.67 ; 257/101 ; 257/103 ; 313/499		Herzog, Arno Henry	

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	Search Terms	Total	USPAT	USOCR	EPO
1	GRAPH	178539			
2	P-SURFACE	42			
3	SURFACE	1588120			
4	(4 AND 3)	11	<u> </u>	ž	